

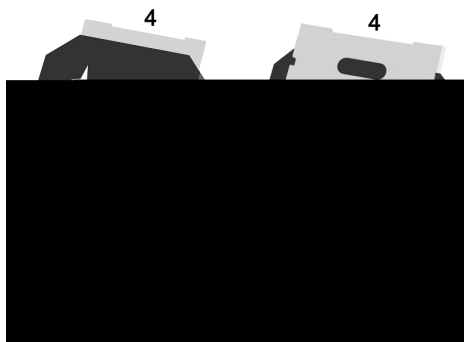
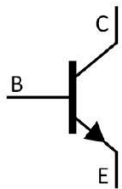
Rev.B Apr.-2023

TO-252      NPN      Silicon NPN transistor in a TO-252 Plastic Package.

### AEC-Q101

High collector-Emitter breakdown voltage, Suitable for transformer, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

High voltage general purpose applications, Meet the stringent requirements of automotive applications.



PIN1   Base      PIN 2,4   Collector      PIN 3   Emitter

See Marking Instructions.

| Parameter                      | Symbol                                | Rating  | Unit |
|--------------------------------|---------------------------------------|---------|------|
| Collector to Base Voltage      | $V_{CBO}$                             | 300     | V    |
| Collector to Emitter Voltage   | $V_{CEO}$                             | 300     | V    |
| Emitter to Base Voltage        | $V_{EBO}$                             | 5.0     | V    |
| Collector Current - Continuous | $I_C$                                 | 500     | mA   |
| Collector Power Dissipation    | $P_C$                                 | 1.56    | W    |
| Collector Power Dissipation    | $P_C(T_C=25\text{ }^{\circ}\text{C})$ | 15      | W    |
| Junction Temperature           | $T_j$                                 | 150     |      |
| Storage Temperature Range      | $T_{stg}$                             | -55 150 |      |

Parameter

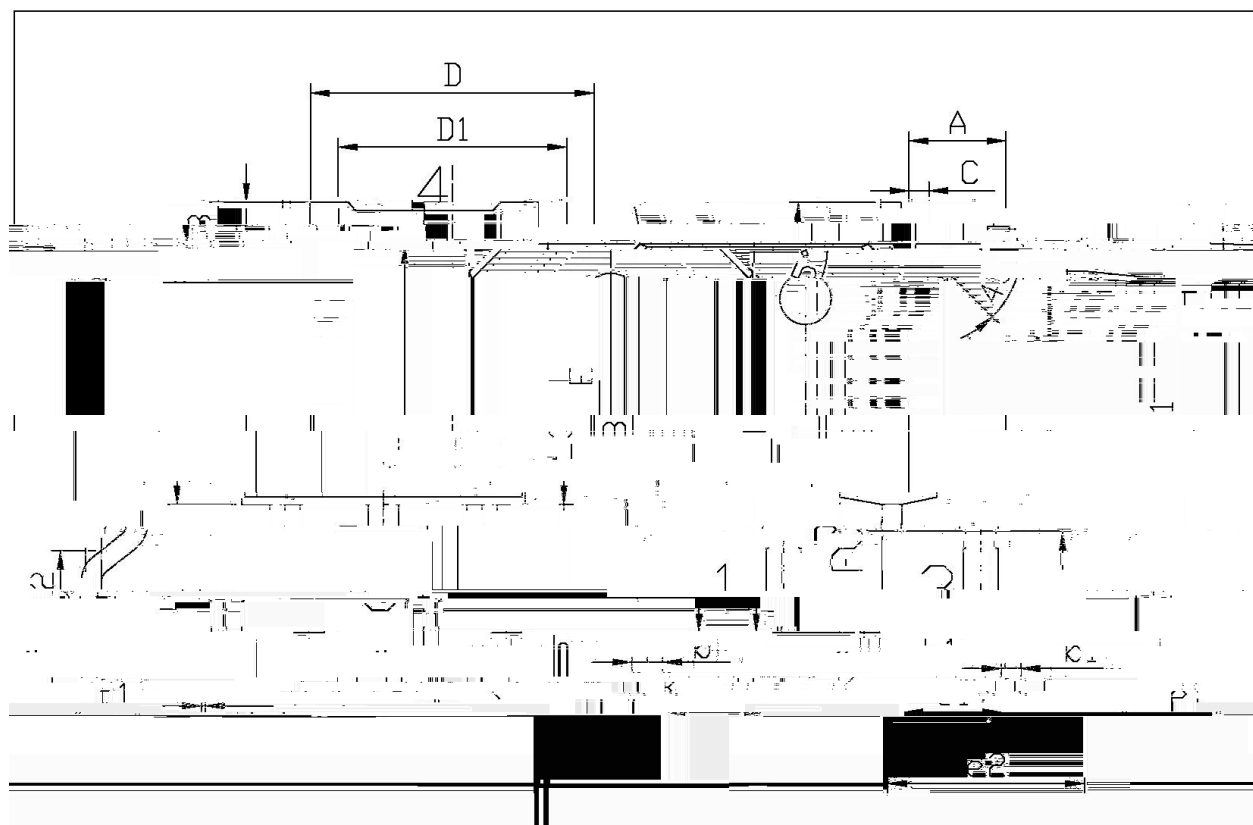
Symbol

Test Conditions

Min

Typ

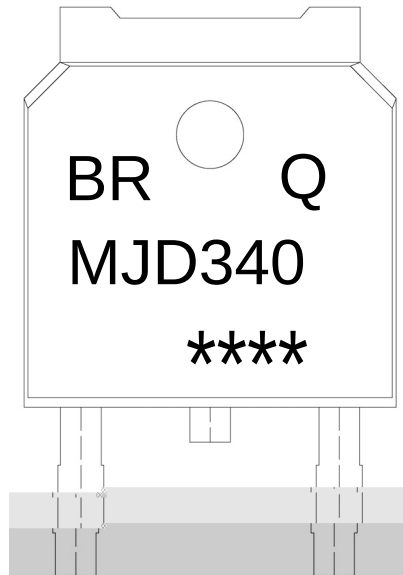




单位: mm

[illegible]

T0-252



BR

Q

MJD340

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Note:

BR: Company Code

Q: Automobile halogen-free product Code

MJD340: Product Type

\*\*\*\*: Lot No. Code, code change with Lot No

